

**AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions and listings of claims in this application.

1. (Currently Amended) A method for removing boron from silicon, comprising heating metal silicon containing boron as an impurity to a temperature ranging from the melting point of silicon to 2200°C to place it in a molten state, then adding a solid comprising silicon dioxide and a solid comprising one or both of a carbonate of an alkali metal or a hydrate of a carbonate of an alkali metal into said molten silicon so as to form a slag containing boron on said molten silicon and remove the boron from the silicon, wherein any solid added to the molten silicon is not a ~~chloride~~ solid that generates a chloride containing gas when added to molten silicon.

2. (Previously Presented) The method for removing boron from silicon as set forth in claim 1, wherein the formed slag is discharged.

3. (Previously Presented) The method for removing boron from silicon as set forth in claim 2, wherein the interval from adding the solid consisting essentially of silicon dioxide and the solid consisting essentially of one or both of a carbonate of an alkali metal or a hydrate of a carbonate of an alkali metal to then discharging the formed slag is 5 minutes or more.

4. (Previously Presented) The method for removing boron from silicon as set forth in claim 1, wherein the solid consisting essentially of silicon dioxide and the solid consisting essentially of one or both of a carbonate of an alkali metal or a hydrate of a carbonate of an alkali metal are added simultaneously.

5. (Previously Presented) The method for removing boron from silicon as set forth in claim 1, wherein the solid consisting essentially of silicon dioxide and the solid consisting essentially of one or both of a carbonate of an alkali metal or a hydrate of a carbonate of an alkali metal are added separately.

6. (Original) The method for removing boron from silicon as set forth in claim 5, wherein the interval of said addition is within 30 minutes.

7. (Previously Presented) The method for removing boron from silicon as set forth in claim 1, wherein the addition of the solid consisting essentially of silicon dioxide and the solid consisting essentially of one or both of a carbonate of an alkali metal or a hydrate of a carbonate of an alkali metal is divided into two or more operations.

8. (Previously Presented) The method for removing boron from silicon as set forth in claim 7, wherein the already formed slag is discharged, and then the solid consisting essentially of silicon dioxide and the solid consisting essentially of one or both of a carbonate of an alkali metal or a hydrate of a carbonate of an alkali metal are newly added.

9. (Previously Presented) The method for removing boron from silicon as set forth in claim 8, wherein the interval from when adding the solid consisting essentially of silicon dioxide and the solid consisting essentially of one or both of a carbonate of an alkali metal or a hydrate of a carbonate of an alkali metal to molten silicon to then discharging the formed slag is 5 minutes or more.

10. (Previously Presented) The method for removing boron from silicon as set forth in claim 8, the process of adding the solid consisting essentially of silicon dioxide and the solid consisting essentially of one or both of a carbonate of an alkali metal or a hydrate of a carbonate of an alkali metal to form slag is performed, and then the slag is discharged a plurality of times.

11. (Previously Presented) The method for removing boron from silicon as set forth in claim 10, wherein while performing the processing of adding the solid consisting essentially of silicon dioxide and the solid consisting essentially of one or both of a carbonate of an alkali metal or a hydrate of a carbonate of an alkali metal to form slag, then discharging the slag a plurality of times, the concentration of boron in the molten silicon becomes 1 mass ppm or less.

12. (Previously Presented) The method for removing boron from silicon as set forth in claim 1, wherein the solid consisting essentially of silicon dioxide and the solid consisting essentially of one or both of a carbonate of an alkali metal or a hydrate of a carbonate of an alkali metal are added in amounts whereby the formed slag does not completely cover the surface of the molten silicon.

13. (Original) The method for removing boron from silicon as set forth in claim 1, wherein a mole of silicon in the silicon dioxide added is 0.05 to 20 times the mole of the alkali element in one or both of the carbonate of an alkali metal and the hydrate of a carbonate of an alkali metal.

14. (Original) The method for removing boron from silicon as set forth in claim 1, wherein the alkali element of one or both of the carbonate of an alkali metal and the hydrate of a carbonate of an alkali metal is one or more of lithium, sodium, and potassium.

15. (Original) The method for removing boron from silicon as set forth in claim 14, wherein one or both of the carbonate of an alkali metal and the hydrate of a carbonate of an alkali metal is one or more of lithium carbonate, sodium carbonate, potassium carbonate, lithium bicarbonate, sodium bicarbonate, potassium bicarbonate, or their hydrates.

16. (Canceled)